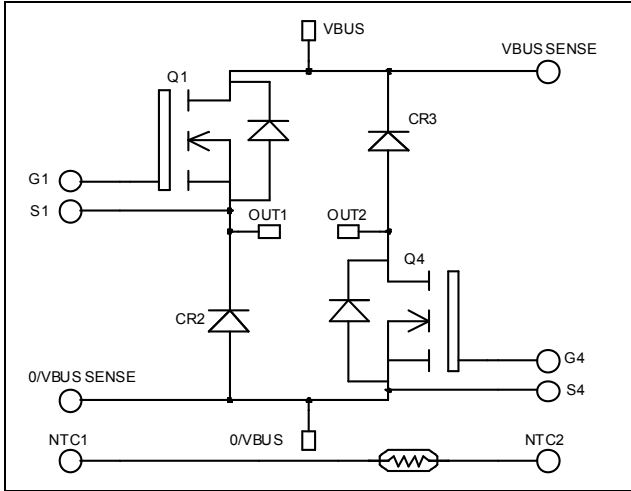


***Asymmetrical - Bridge
MOSFET Power Module***

**$V_{DSS} = 500V$
 $R_{DSon} = 75m\Omega \text{ max @ } T_j = 25^\circ C$
 $I_D = 46A \text{ @ } T_c = 25^\circ C$**



Application

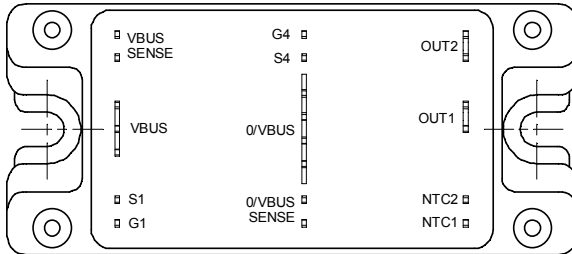
- Welding converters
- Switched Mode Power Supplies
- Switched Reluctance Motor Drives

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile



Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	500	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	46
		$T_c = 80^\circ C$	34
I_{DM}	Pulsed Drain current	184	A
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	75	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	357
I_{AR}	Avalanche current (repetitive and non repetitive)	46	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	2500	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV_{DSS}	Drain - Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	500			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 500V$			100	μA
		$V_{GS} = 0V, V_{DS} = 400V$			500	
$R_{DS(on)}$	Drain - Source on Resistance	$V_{GS} = 10V, I_D = 23A$			75	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5mA$	3		5	V
I_{GSS}	Gate - Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		5600		pF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		1200		
C_{rss}	Reverse Transfer Capacitance	$f = 1MHz$		90		
Q_g	Total gate Charge	$V_{GS} = 10V$		123		nC
Q_{gs}	Gate - Source Charge	$V_{Bus} = 250V$		33		
Q_{gd}	Gate - Drain Charge	$I_D = 46A$		65		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 333V$ $I_D = 46A$ $R_G = 5\Omega$		18		ns
T_r	Rise Time			35		
$T_{d(off)}$	Turn-off Delay Time			87		
T_f	Fall Time			77		
E_{on}	Turn-on Switching Energy ①	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 46A, R_G = 5\Omega$		755		μJ
E_{off}	Turn-off Switching Energy ②			726		
E_{on}	Turn-on Switching Energy ①	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 46A, R_G = 5\Omega$		1241		μJ
E_{off}	Turn-off Switching Energy ②			846		

Diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle, $T_c = 70^\circ\text{C}$		60		A
V_F	Diode Forward Voltage	$I_F = 60A$		1.6	1.8	V
		$I_F = 120A$		1.9		
		$I_F = 60A$, $T_j = 125^\circ\text{C}$		1.4		
t_{rr}	Reverse Recovery Time	$I_F = 60A$, $V_R = 400V$, $di/dt = 200A/\mu s$	$T_j = 25^\circ\text{C}$	130		ns
			$T_j = 125^\circ\text{C}$	170		
Q_{rr}	Reverse Recovery Charge	$I_F = 60A$, $V_R = 400V$, $di/dt = 200A/\mu s$	$T_j = 25^\circ\text{C}$	220		nC
			$T_j = 125^\circ\text{C}$	920		

① E_{on} includes diode reverse recovery.

② In accordance with JEDEC standard JESD24-1.

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R _{thJC}	Junction to Case	Transistor		0.35	°C/W	
		diode		0.9		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1mA, 50/60Hz	2500			V	
T _J	Operating junction temperature range	-40		150	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque		To Heatsink	M5	4.7	N.m
Wt	Package Weight				160	g

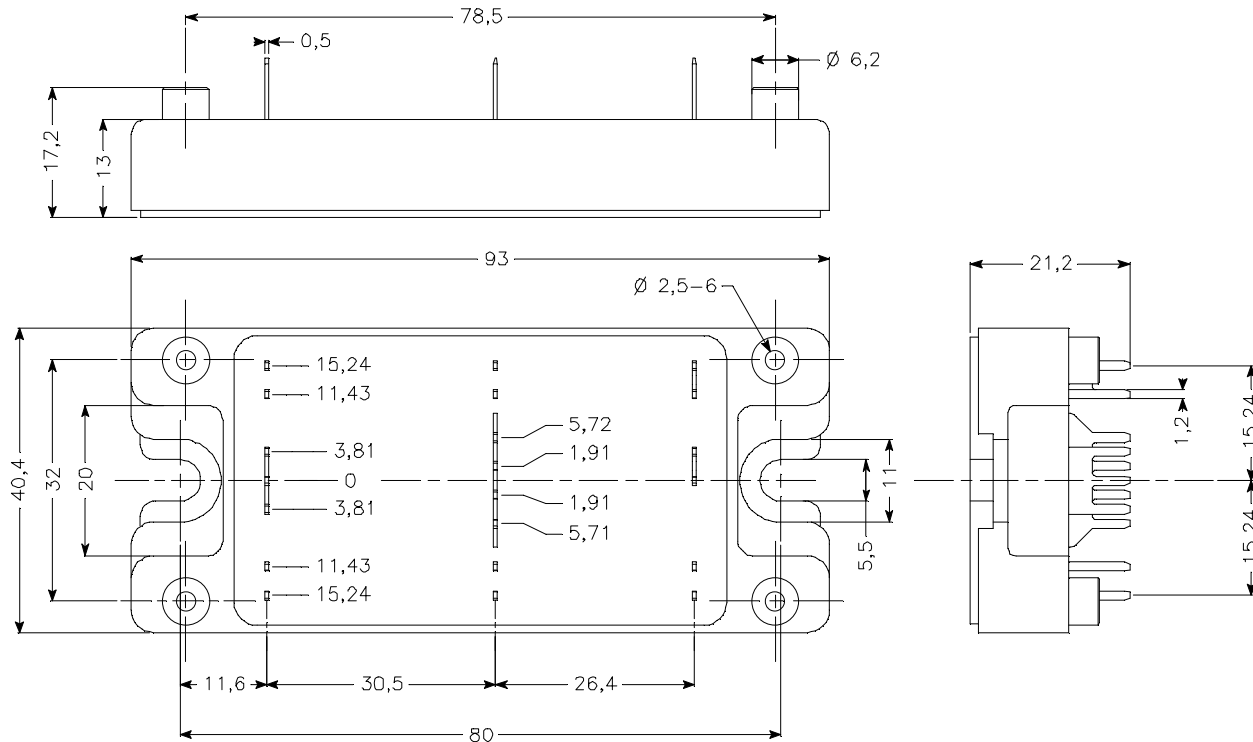
Temperature sensor NTC

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		68		kΩ
B _{25/85}	T ₂₅ = 298.16 K		4080		K

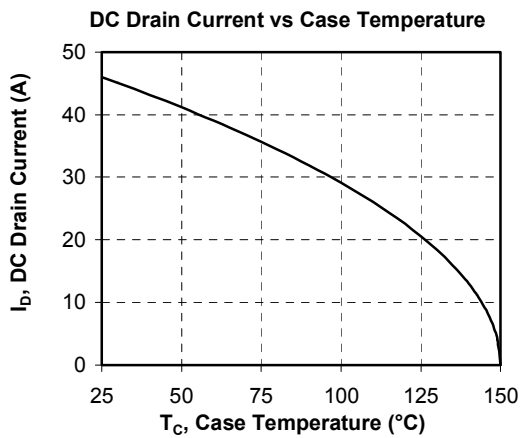
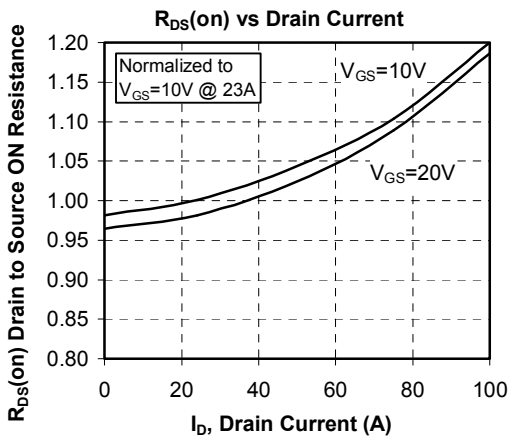
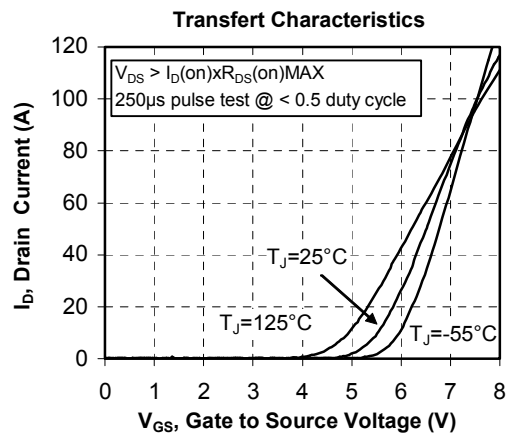
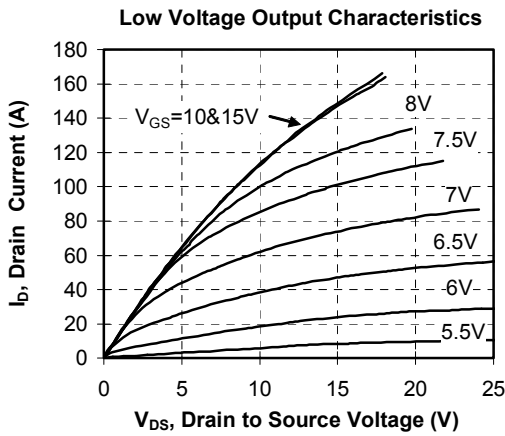
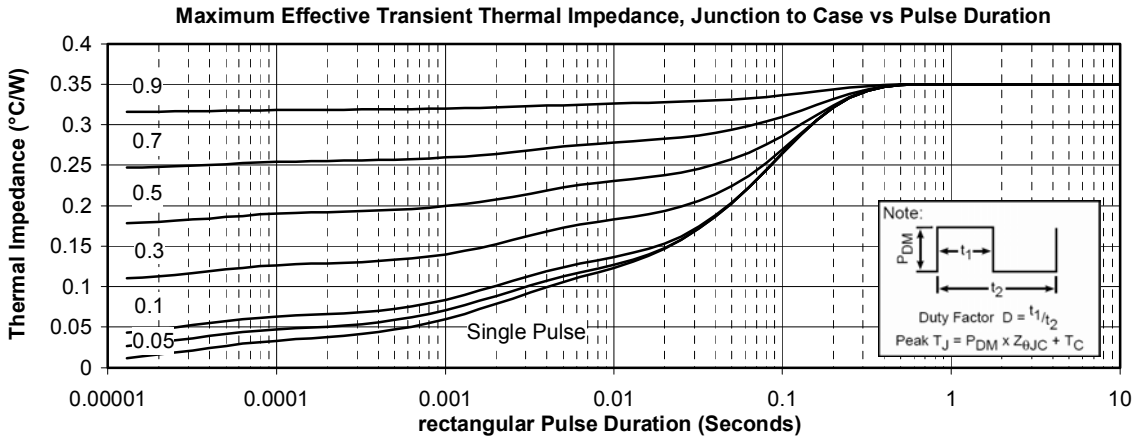
$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

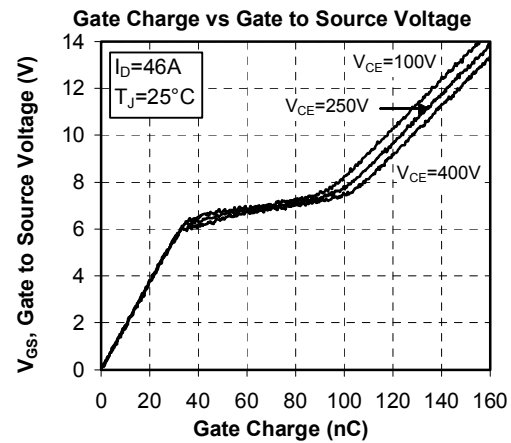
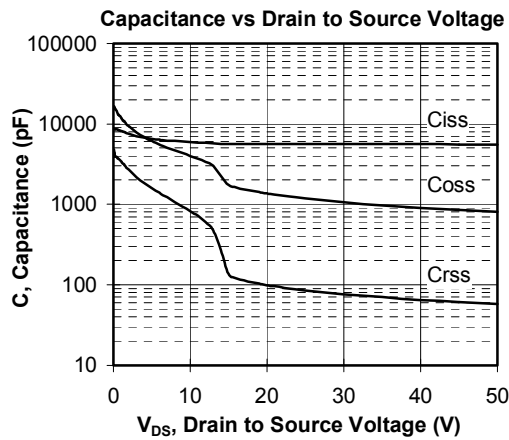
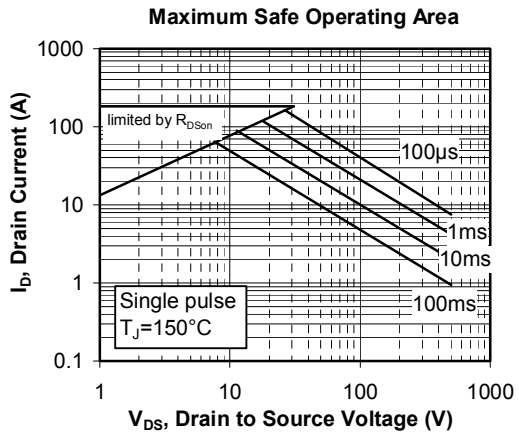
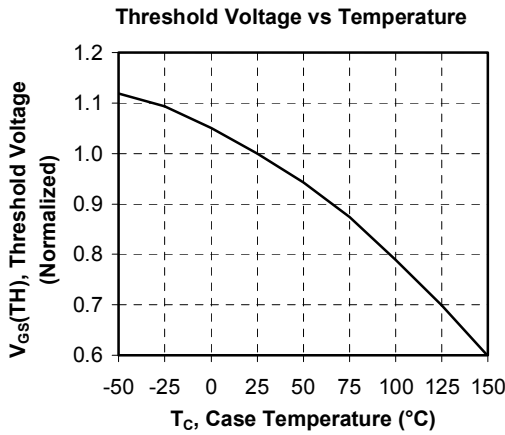
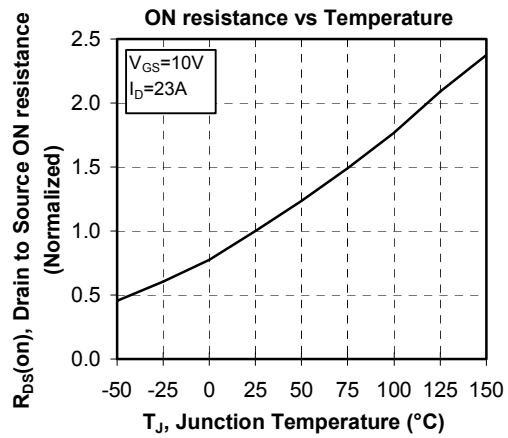
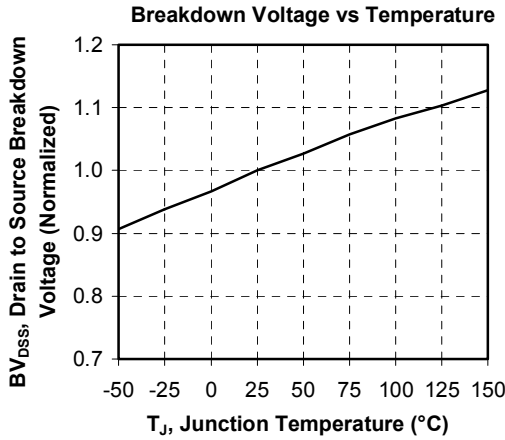
T: Thermistor temperature
R_T: Thermistor value at T

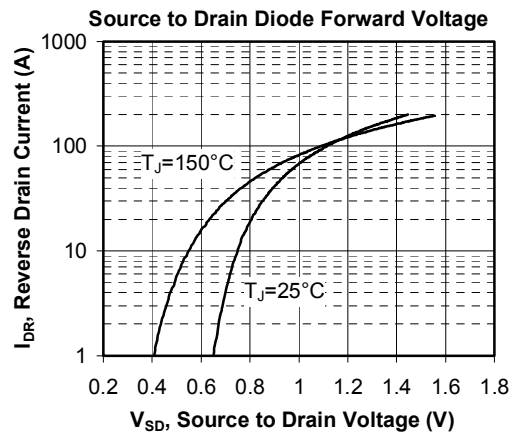
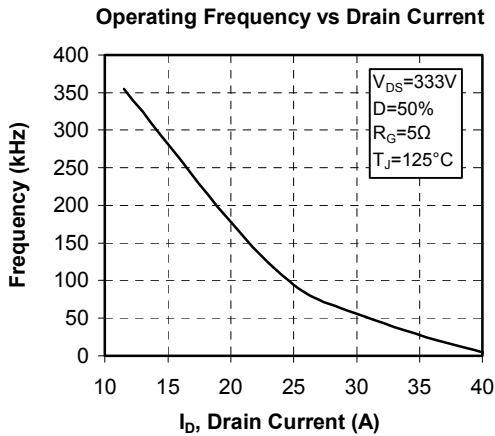
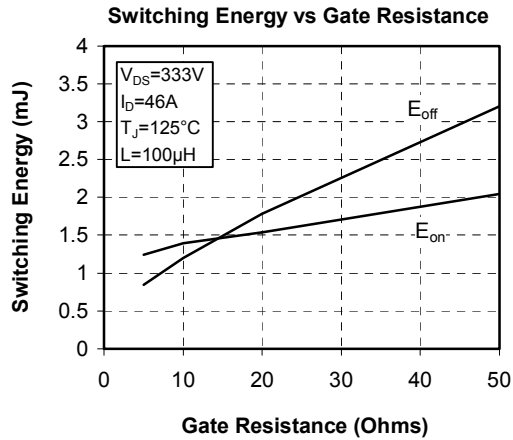
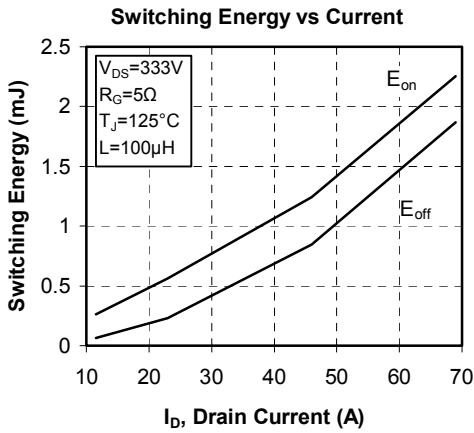
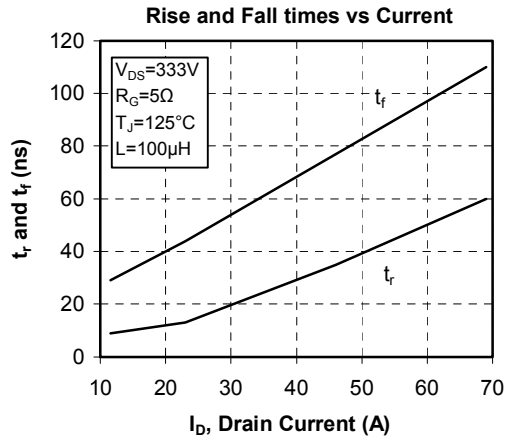
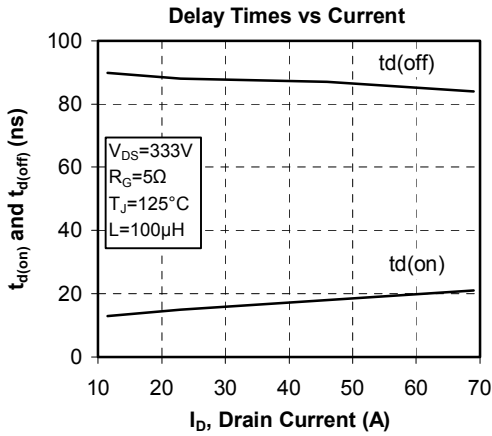
Package outline



Typical Performance Curve







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APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.